

2MBI200VH-120-50

IGBT Modules

IGBT MODULE (V series) 1200V / 200A / 2 in one package

Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



Maximum Ratings and Characteristics

Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units	
Collector-Emitte	er voltage	Vces			1200		
Gate-Emitter voltage		V _{GES}			±20	V	
	rent	Ic	Continuous	Tc=100°C	200		
#			Continuous	Tc=25°C	240		
≥ Collector currer		Ic pulse	1ms		400	Α	
드		-lc					
		-lc pulse	1ms		400		
Collector power dissipation		Pc	1 device		1110	W	
Junction temperature		Tj			175		
Operating junction temperature (under switching conditions)		Tjop			150	°C	
Case temperature		Tc			125	<u> </u>	
Storage temperature		Tstg			-40 ~ +125		
Isolation voltage between terminal and copper base (*1)		Viso	AC: 1min.		2500	VAC	
Sorow torque	Nounting (*2)				6.0	N m	
Screw torque	erminals (*3)]-			5.0	IN III	

Note *1: All terminals should be connected together during the test. Note *2: Recommendable Value : 3.0-6.0 Nm (M5 or M6) Note *3: Recommendable Value : 2.5-5.0 Nm (M6)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

ems	Cumbala	Canditions		Characteristics		Unite	
eilis	Symbols	Conditions		min.	typ.	max.	Units
Zero gate voltage collector current ICES VGE = 0V, VGE = 1		V _{GE} = 0V, V _{CE} = 1200V	0V, V _{CE} = 1200V		-	2.0	mA
Gate-Emitter leakage current	Iges	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	400	nA
Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 200mA		6.0	6.5	7.0	V
	V	V _{GE} = 15V I _C = 200A	Tj=25°C	-	1.95	2.40	V
	V _{CE (sat)} (terminal)		Tj=125°C	-	2.25	-	
Collector-Emitter saturation voltage	(terrillial)		Tj=150°C	-	2.30	-	
Collector-Enlitter Saturation Voltage	V _{CE (sat)} (chip)		Tj=25°C	-	1.75	2.15	
			Tj=125°C	-	2.05	-	
			Tj=150°C	-	2.10	-	
Internal gate resistance	R _{g(int)} -			-	3.8	-	Ω
Input capacitance	Cies	$V_{CE} = 10V$, $V_{GE} = 0V$, $f = 1MHz$		-	18.2	-	nF
5	ton			-	0.60	-	
Turn-on time	tr	$V_{\text{CC}} = 600\text{V}, \text{ Ic} = 200\text{A}$ $V_{\text{GE}} = \pm 15\text{V}, \text{ Rg} = 2.7\Omega$ $Tj = 150^{\circ}\text{C}, \text{ Ls} = 30\text{nH}$		-	0.20	-	µsec
	tr (i)			-	0.05	-	
Turn-off time	toff			-	0.80	-	
Turn-on time	tf			-	0.08	-	
	VF	V _{GE} = 0V I _F = 200A	Tj=25°C	-	1.85	2.30	V
	(terminal)		Tj=125°C	-	2.00	-	
Forward on voltage	(terrillial)		Tj=150°C	-	1.95	-	
	VF		Tj=25°C	-	1.70	2.15	
			Tj=125°C	-	1.85	-	
	(chip)		Tj=150°C	-	1.80	-	
Reverse recovery time	trr	I _F = 200A		-	0.15	-	usec

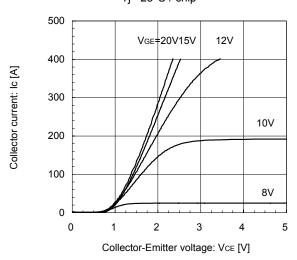
Thermal resistance characteristics

	Symbols		Characteristics			Units
Items		Conditions				
itomo		Conditions	min.	typ.	max.	Oiiits
Thermal resistance (1device)	Dth(i o)	IGBT	-	-	0.135	°C/W
Thermal resistance (Tuevice)	Rth(j-c)	FWD	-	-	0.200	
Contact thermal resistance (1device) (*4)	Rth(c-f)	with Thermal Compound	-	0.0250	-	

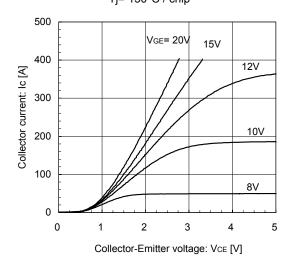
Note *4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

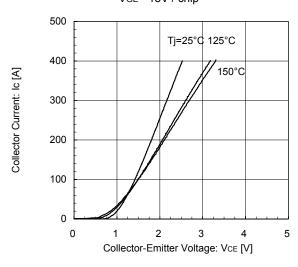
Collector current vs. Collector-Emitter voltage (typ.) Tj= 25°C / chip



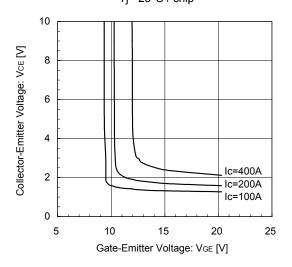
Collector current vs. Collector-Emitter voltage (typ.) Tj= 150°C / chip



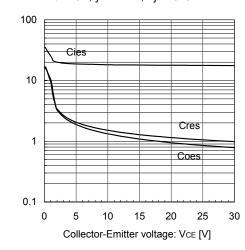
Collector current vs. Collector-Emitter voltage (typ.) VGE= 15V / chip



Collector-Emitter voltage vs. Gate-Emitter voltage (typ.) Tj= 25°C / chip

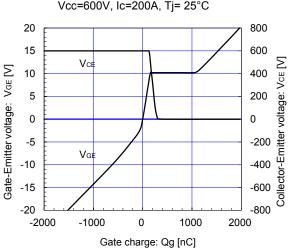


Gate Capacitance vs. Collector-Emitter Voltage (typ.) $V_{GE}=0V, f=1MHz, Tj=25^{\circ}C$

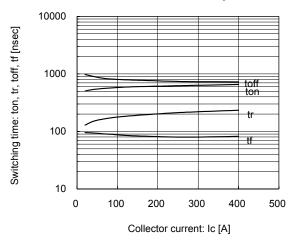


Gate Capacitance: Cies, Coes, Cres [nF]

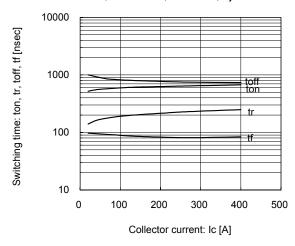
Dynamic Gate Charge (typ.) Vcc=600V, Ic=200A, Tj= 25°C



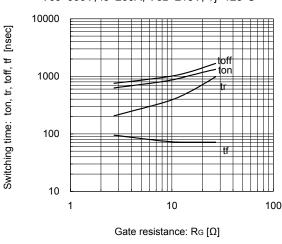
Switching time vs. Collector current (typ.) Vcc=600V, VgE= \pm 15V, Rg= 2.7Ω , Tj= 125° C



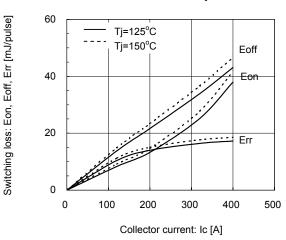
Switching time vs. Collector current (typ.) Vcc=600V, $VgE=\pm15V$, $Rg=2.7\Omega$, $Tj=150^{\circ}C$



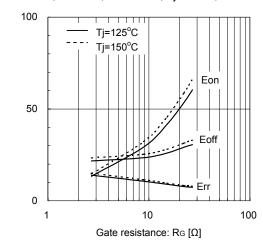
Switching time vs. Gate resistance (typ.) Vcc=600V, Ic=200A, VgE=±15V, Tj=125°C



Switching loss vs. Collector current (typ.) Vcc=600V, VgE=±15V, Rg=2.7Ω, Tj=125°C, 150°C

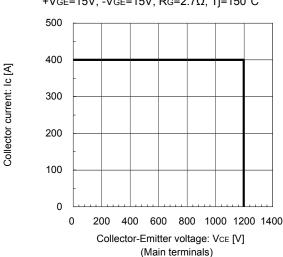


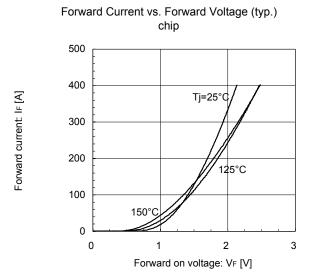
Switching loss vs. Gate resistance (typ.) Vcc=600V, Ic=200A, VgE=±15V, Tj=125°C, 150°C



Switching loss: Eon, Eoff, Err [mJ/pulse]

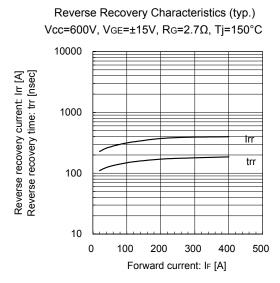
Reverse bias safe operating area (max.) $+V_{GE}=15V$, $-V_{GE}=15V$, $R_{G}=2.7\Omega$, $T_{J}=150^{\circ}C$

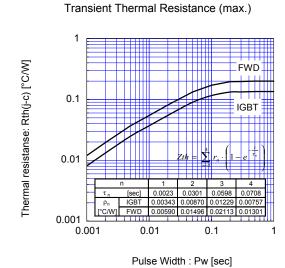


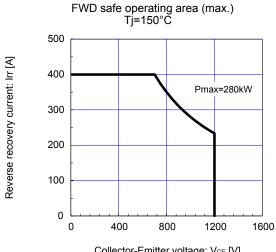


Vcc=600V, VgE=±15V, Rg=2.7Ω, Tj=125°C 10000 Reverse recovery current: Irr [A] Reverse recovery time: trr [nsec] 1000 Irr trr 100 10 0 100 200 300 400 500 Forward current: IF [A]

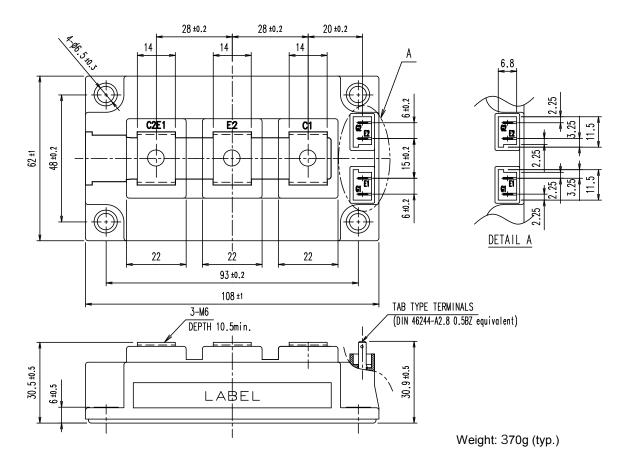
Reverse Recovery Characteristics (typ.)



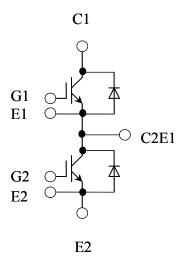




■ Outline Drawings (Unit: mm)



■ Equivalent Circuit



http://www.fujielectric.com/products/semiconductor/

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